

**1. Material** Substrate GaAs (N Type)  
 Epitaxial Layer GaAs (P/N Type)

**2. Electrode** N(Cathode) Side Gold Alloy  
 P(Anode) Side Aluminum Alloy

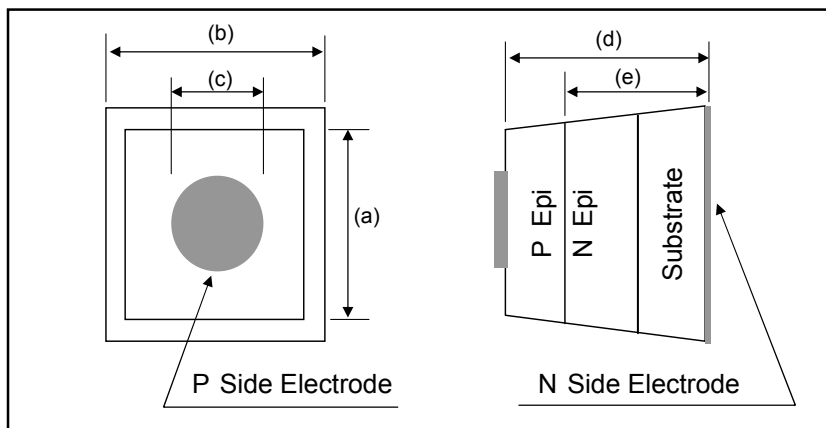
**3. Electro-Optical Characteristics**

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_F$		1.25	1.35	V	IF=20mA
Reverse Voltage	$V_R$	8			V	IR=10uA
Power	Po	A	1.09		mW	IF=20mA
		B	1.17			
		C	1.24			
		D	1.32			
		E	1.39			
		F	1.47			
		G	1.55			
		G1	1.64			
Wavelength	$\lambda_P$		940		nm	IF=20mA
	$\Delta\lambda$		45		nm	IF=20mA

※ Note : LED Chip is mounted on TO-18 gold header without resin coating

**4. Mechanical Data**

- (a) Emission Area ----- 8mil x 8mil
- (b) Bottom Area ----- 9mil x 9mil
- (c) Bonding Pad ----- 100um
- (d) Chip Thickness ----- 9mil
- (e) Junction Height ----- 6.0mil



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